# CS354: Machine Organization and Programming

Lecture 18 Wednesday the October 14<sup>th</sup> 2015

Section 2 Instructor: Leo Arulraj © 2015 Karen Smoler Miller © Some examples, diagrams from the CSAPP text by Bryant and O'Hallaron

## **Class Announcements**

- 1. Programming Assignment 1 Grades and Feedback distributed in class. You can collect it from me during office hours too.
- 2. How many of you have started working on Programming Assignment 2? Solved 1, 2, 3, 4 bombs?

### Lecture Overview

- 1. Stack Smashing Real Example
- 2. Ways to thwart Stack Smashing
- 3. Intro to Storage Technology: SRAM, DRAM, Disks

# SRAM

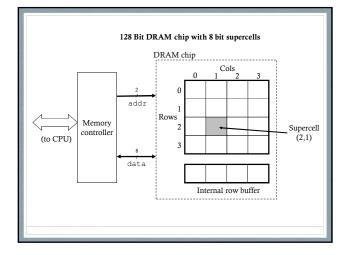
- 1. Six transistor circuit to store a single bit
- 2. **Bi-stable memory cell:** Can tolerate disturbances due to electrical noise, voltage perturbations etc.
- 3. **Persistent:** Retains value indefinitely
- 4. Faster and More expensive than DRAM
- 5. Uses: CPU Caches

# DRAM

- 1. A capacitor to store a single bit and a transistor to access the bit
- 2. Sensitive to disturbances in voltage, electrical noise etc.
- 3. Not persistent: Value must be refreshed every 10-100ms
- 4. Slower and less expensive than SRAM
- 5. Uses: Main memory, frame buffers

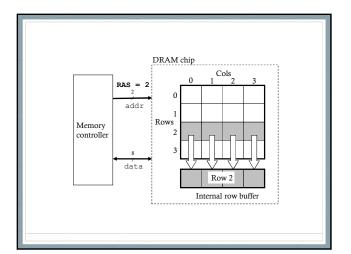
# Conventional DRAM

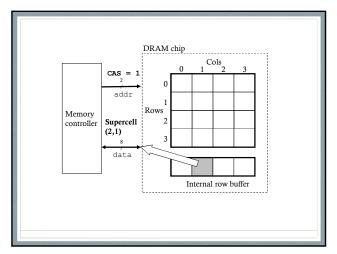
- *I. d* supercells each of *w* DRAM cells storing a total of *dw* bits of information.
- 2. Organized as a rectangular array of *r* rows and *c* columns.
- 3. Memory controller transfers *w* bits at a time to and from the DRAM chip.
- 4. Row address *i* is called a *RAS(Row Access Strobe) Request.*
- 5. Column address *j* is called a *CAS(Column Access Strobe) Request.*
- 6. Arranging DRAM in rows and columns allows lesser address pins but increases access time.



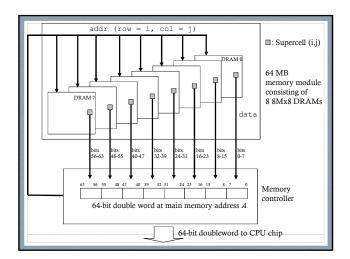
# Conventional DRAM (Shown diagrammatically in next two slides)

- 1. Send RAS i=2
- 2. Entire row is fetched in to the Internal Row Buffer
- 3. Send CAS j=1
- 4. The 8-bits in the supercell (2,1) are sent through the data pins.





# Memory Modules 1. DRAMs packaged into memory modules that plugin into expansion slots in motherboard. (Data at Address A is split in bytes and each byte is stored into each of the DRAM chips in the same supercell.) Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the DRAM chips in the same supercell. Image: Comparison of the



# Enhanced DRAM

- 1. Fast Page DRAM: consecutive accesses to same row is fast by skipping the RAS
- Extended data out DRAM: CAS signals closer in time
   Synchronous DRAM(SDRAM): control signals sent with rising edges of the memory controller's clock
- with rising edges of the memory controller's clock making it fast.
  Double Data-Rate Synchronous DRAM(DDR
- 4. Double Data-Rate Synchronous DRAM( DDR SDRAM): both clock edges used as control signals
- 5. **Rambus DRAM(RDRAM)**: alternative proprietary technology with higher maximum bandwidth
- 6. Video RAM: Allows concurrent reads and writes. Output produced by shifting entire contents of internal buffer in sequence.

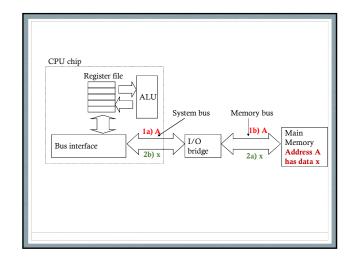
# Non-volatile Memory

- 1. **PROM:** Programmable Read only Memory
- 2. **EPROM**: Erasable Programmable ROM (Reprogrammable 1000 times)
- 3. **EEPROM:** Electrically Erasable Programmable ROM (Reprogrammable 100000 times)
- 4. Flash Memory: based on EEPROMs and found in digital cameras, phones, ipods etc.
- 5. Solid State Drives: Alternative to magnetic disks based on flash. We will cover this in more detail later.

# Accessing Main Memory

What happens with: **movl Address A**, **%eax** Bus interface in CPU initiates a **read** transaction with three steps:

- 1. CPU places address A on the system bus and I/O bridge passes it along to memory bus
- 2. Main memory senses address signal, reads address A from the memory bus, fetches data word from the DRAM and writes to the memory bus. I/O bridge passes it along the system bus.
- 3. CPU senses the data on the system bus, reads it and copies into the register %eax.





What happens with: **movl %eax, Address A** Bus interface in CPU initiates a **write** transaction with three steps:

- 1. CPU places address A on the system bus and I/O bridge passes it along to memory bus. Main memory senses address signal, waits for the data to arrive.
- 2. CPU copies the data word in %eax to the system bus and the I/O bridge passes it along.
- 3. Main memory reads the data word from the memory bus and stores the bits in the DRAM supercell.

